

SPICE Model Parameters

Please copy this code from the SPICE model into LTSPICE (version 4) software for simulation of the GB05SHT06-CAL.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0           $
*      $Date:      05-SEP-2013   $
*
*      GeneSiC Semiconductor Inc.
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*      Dulles, VA 20166
*
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*
*      These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
*      OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
*      TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
*      PARTICULAR PURPOSE."
*      Models accurate up to 2 times rated drain current.
*
*      Start of GB05SHT06-CAL SPICE Model
*
*      .SUBCKT GB05SHT06 ANODE KATHODE
D1 ANODE KATHODE GB05SHT06_25C; Call the Schottky Diode Model
D2 ANODE KATHODE GB05SHT06_PIN; Call the PiN Diode Model
*      .MODEL GB05SHT06_25C D
+ IS      1.99E-17      RS      0.12463
+ N       1            IKF     569.082
+ EG      1.2          XTI     3
+ TRS1    0.0035       TRS2    3.87E-05
+ CJO     3.38E-10     VJ      0.41772
+ M       1.5479       FC      0.5
+ TT      1.00E-10     BV      650
+ IBV     1.00E-03     VPK     650
+ IAVE    5            TYPE    SiC_Schottky
+ MFG     GeneSiC_Semiconductor
*      .MODEL GB05SHT06_PIN D
+ IS      1.33E-10     RS      0.31147
+ N       5            IKF     0
+ EG      3.23         XTI     -10
+ FC      0.5          TT      0
+ BV      650          IBV     1.00E-03
+ VPK     650          IAVE    5
+ TYPE    SiC_PiN
*      .ENDS
*
*      End of GB05SHT06-CAL SPICE Model
```